NLU1GU04

Single Unbuffered Inverter

The NLU1GU04 is an advanced high−speed CMOS unbuffered inverter in ultra−small footprint.

This device is well suited for use in oscillator, pulse−shaping and high input impedance amplifier applications. For digital applications, the NLU1GU04 is recommended.

The NLU1GU04 input and output structures provide protection when voltages up to 7.0 V are applied, irregardless of the supply voltage.

Features

- High Speed: t_{PD} = 2.5 ns (Typ) @ V_{CC} = 5.0 V
- Low Power Dissipation: I_{CC} = 1 μA (Max) at T_A = 25°C
- Power Down Protection Provided on inputs
- Balanced Propagation Delays
- Overvoltage Tolerant (OVT) Input and Output Pins
- Ultra−Small Pb−Free Package
- This is a Pb−Free Device

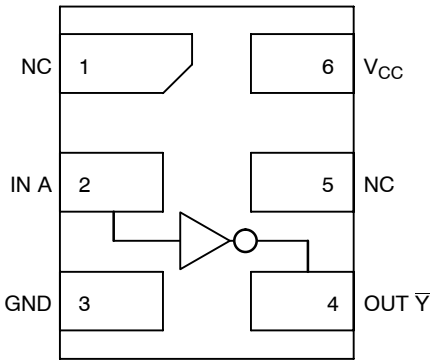


Figure 1. Pinout (Top View)

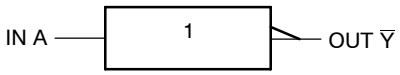
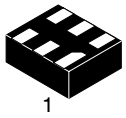


Figure 2. Logic Symbol

ON Semiconductor®

http://onsemi.com

MARKING DIAGRAM



UDFN6
MU SUFFIX
CASE 517AA

U = Device Marking
M = Date Code
▪ = Pb−Free Package

PIN ASSIGNMENT

1	NC
2	IN A
3	GND
4	OUT $\overline{Y}$
5	NC
6	V_{CC}

FUNCTION TABLE

A	$\overline{Y}$
L	H
H	L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +7.0	V
V_{IN}	DC Input Voltage		−0.5 to +7.0	V
V_{OUT}	DC Output Voltage		−0.5 to +7.0	V
I_{IK}	DC Input Diode Current	V_{IN} < GND	−20	mA
I_{OK}	DC Output Diode Current	V_{OUT} < GND	±20	mA
I_O	DC Output Source/Sink Current		±12.5	mA
I_{CC}	DC Supply Current Per Supply Pin		±25	mA
I_{GND}	DC Ground Current per Ground Pin		±25	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		TBD	°C
T_J	Junction Temperature Under Bias		TBD	°C
θ_{JA}	Thermal Resistance (Note 1)	UDFN6	TBD	°C/W
P_D	Power Dissipation in Still Air at 85°C	UDFN6	TBD	mW
MSL	Moisture Sensitivity		Level 1	
F_R	Flammability Rating Oxygen	Index: 28 to 34	UL 94 V−0 @ 0.125 in	
V_{ESD}	ESD Withstand Voltage Human Body Mode (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)		> 2000 > 200 N/A	V
$I_{LATCHUP}$	Latchup Performance Above V_{CC} and Below GND at 125 °C (Note 5)		±500	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm−by−1 inch, 2 ounce copper trace no air flow.
2. Tested to EIA / JESD22−A114−A.
3. Tested to EIA / JESD22−A115−A.
4. Tested to JESD22−C101−A.
5. Tested to EIA / JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	Positive DC Supply Voltage		1.65	5.5	V
V_{IN}	Digital Input Voltage		0	5.5	V
V_{OUT}	Output Voltage		0	5.5	V
T_A	Operating Free−Air Temperature		−55	+125	°C
$\Delta t/\Delta V$	Input Transition Rise or Fail Rate	V_{CC} = 3.3 V ± 0.3 V V_{CC} = 5.0 V ± 0.5 V	0 0	100 20	ns/V

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Conditions	V_{CC} (V)	T_A = 25 °C			T_A = +85°C		T_A = −55°C to +125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V_{IH}	Low−Level Input Voltage		1.65 2.3 to 5.5	0.85 x V_{CC} 0.80 x V_{CC}			0.85 x V_{CC} 0.80 x V_{CC}				V
V_{IL}	Low−Level Input Voltage		1.65 2.3 to 5.5			0.15 x V_{CC} 0.20 x V_{CC}		0.15 x V_{CC} 0.20 x V_{CC}		0.15 x V_{CC} 0.20 x V_{CC}	V
V_{OH}	High−Level Output Voltage	V_{IN} = V_{IH} or V_{IL} I_{OH} = −50 μA	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		V_{IN} = V_{IH} or V_{IL} I_{OH} = −4 mA I_{OH} = −8 mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
V_{OL}	Low−Level Output Voltage	V_{IN} = V_{IH} or V_{IL} I_{OL} = 50 μA	2.0 3.0 4.5		0 0 0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		V_{IN} = V_{IH} or V_{IL} I_{OL} = 4 mA I_{OL} = 8 mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I_{IN}	Input Leakage Current	0 ≤ V_{IN} ≤ 5.5 V	0 to 5.5			±0.1		±1.0		±1.0	μA
I_{CC}	Quiescent Supply Current	0 ≤ V_{IN} ≤ V_{CC}	5.5			1.0		20		40	μA

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3.0 ns)

Symbol	Parameter	V_{CC} (V)	Test Condition	T_A = 25 °C			T_A = +85°C		T_A = −55°C to +125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t_{PLH}, t_{PHL}	Propagation Delay, Input A to Output $\overline{Y}$	3.0 to 3.6	C_L = 15 pF		3.5	8.9		10.5		12	ns
			C_L = 50 pF		4.8	11.4		13		15.5	
		4.5 to 5.5	C_L = 15 pF		2.5	5.5		6.5		8.0	
			C_L = 50 pF		3.8	7.0		8.0		9.5	
C_{IN}	Input Capacitance				4	10		10		10	pF
C_{PD}	Power Dissipation Capacitance (Note 6)	5.0			22						pF

6. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the dynamic operating current consumption without load. Average operating current can be obtained by the equation $I_{CC(OPR)}$ = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no−load dynamic power consumption: P_D = C_{PD} • V_{CC}^2 • f_{in} + I_{CC} • V_{CC}.

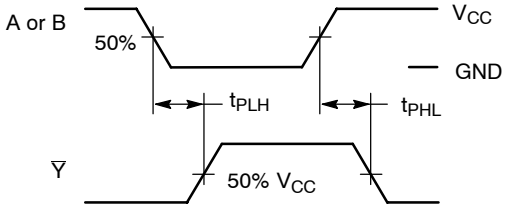
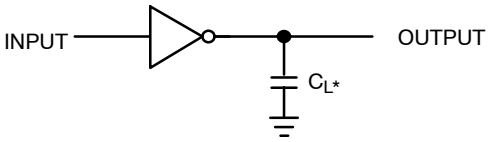


Figure 3. Switching Waveforms



*Includes all probe and jig capacitance.
A 1−MHz square input wave is recommended for propagation delay tests.

Figure 4. Test Circuit

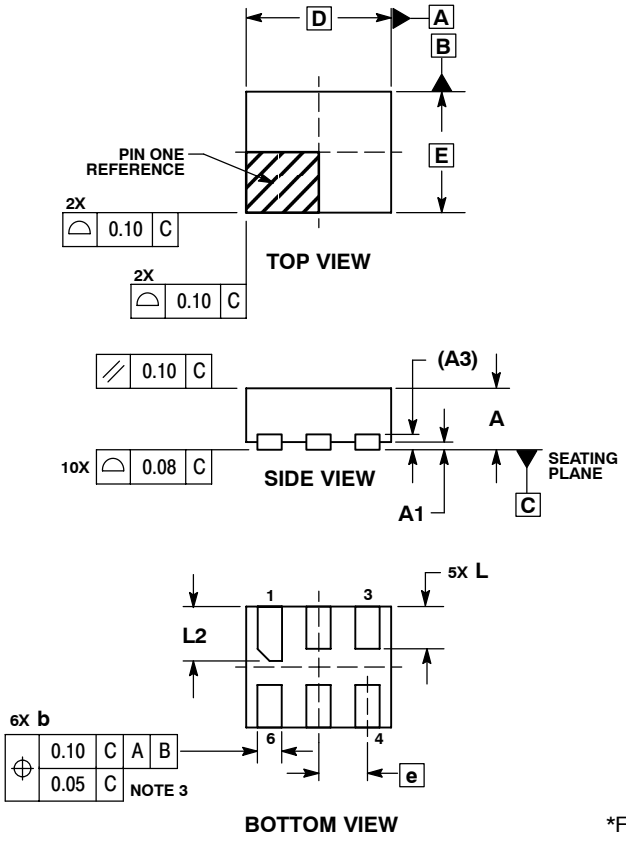
ORDERING INFORMATION

Device	Package	Shipping†
NLU1GU04MUTCG	UDFN6 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

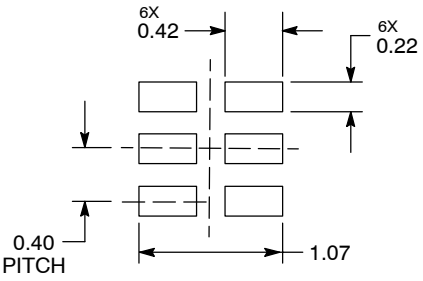
UDFN6, 1.2x1.0, 0.4P
CASE 517AA−01
ISSUE B



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 mm FROM TERMINAL.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIMETERS	
DIM	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A3	0.127 REF	
b	0.15	0.25
D	1.20 BSC	
E	1.00 BSC	
e	0.40 BSC	
L	0.30	0.40
L2	0.40	0.50

MOUNTING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5773−3850

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

NLU1GU04/D